

RL 4 - Epitaxial growth and nanostructure fabrication

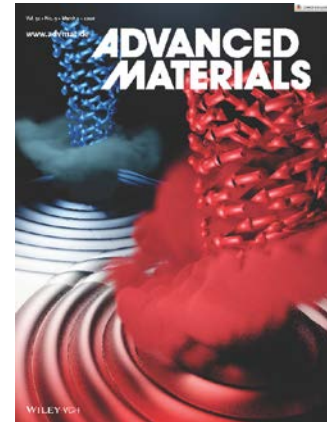
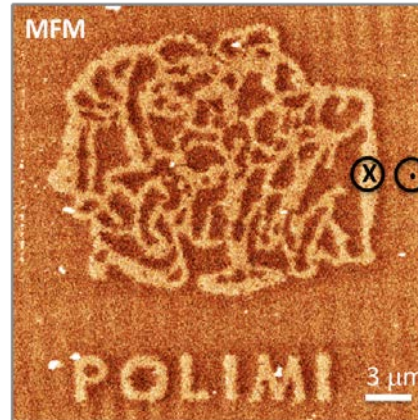
- **Engineering Physics in Nanostructured materials and Devices**
- **Nanomagnetism for Biology and Spintronics**
- **Spin transport in semiconductor-based platforms**
- **Semiconductors nanostructures and devices**
- **2D Nanoelectronics and Nanofabrication**
- **Scanning tunneling microscopy of low-dimensional systems**
- **Photoemission spectroscopies to explore nano-assembled molecular architectures**

Engineering Physics in Nanostructured materials and Devices Group

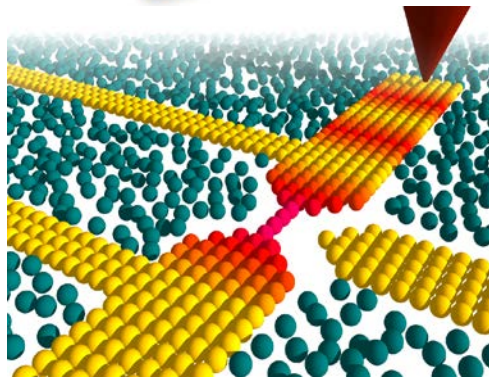
<http://phynd.polimi.it>



- **Nanoscale control of the static and dynamic magnetic properties** of materials.
- **Spin waves and topological quasi-particles** for novel devices for beyond CMOS computing.



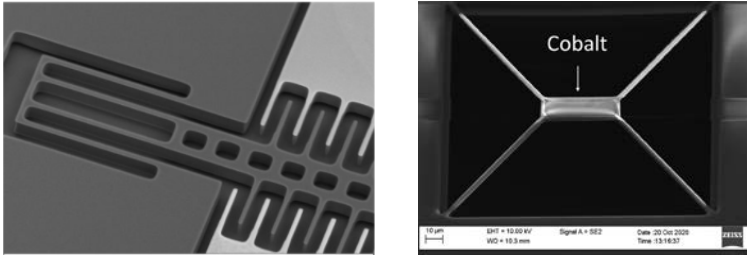
Beyond nanofabrication via nanoscale phase engineering of matter



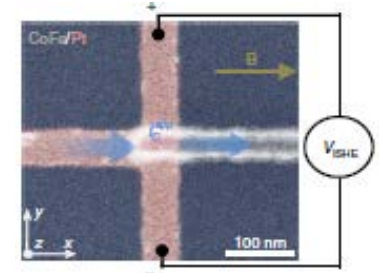
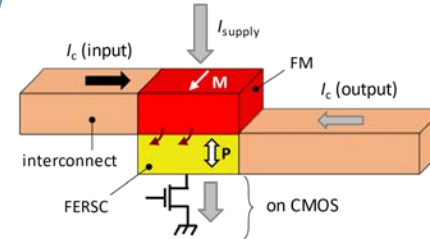
ERC-2020-STG

- Develop a new class of **artificial nanomaterials** with unprecedented electronic transport properties.
- Realize **novel monolithic three-dimensional nanoelectronic platforms** for beyond-CMOS computing.

Nanomagnetism for Biology and Spintronics (<http://nabis.fisi.polimi.it/thesis>)

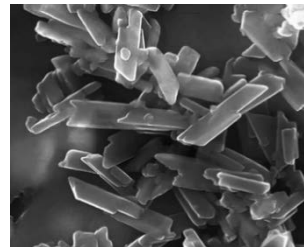


Integration of magnetic materials with MEMS for novel magnetometers and energy-harvesters



Beyond-CMOS computing in nanodevices exploiting the ferroelectric control of spin-to-charge conversion in Rashba semiconductors

Lab-on-chip diagnostic test for Malaria based on the detection of paramagnetic Hemozoin nanocrystals in blood samples.

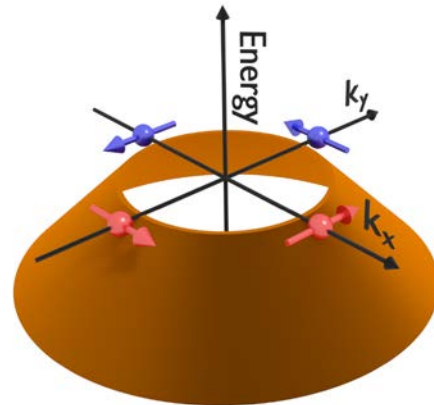
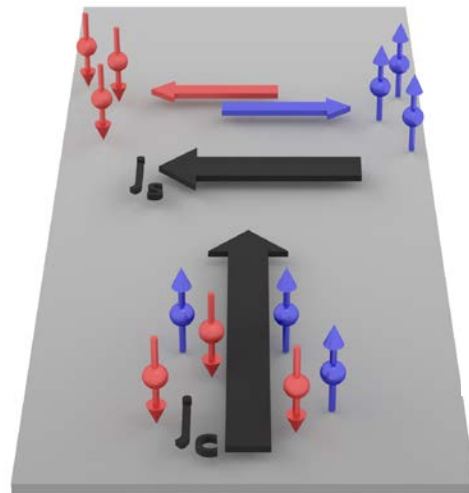
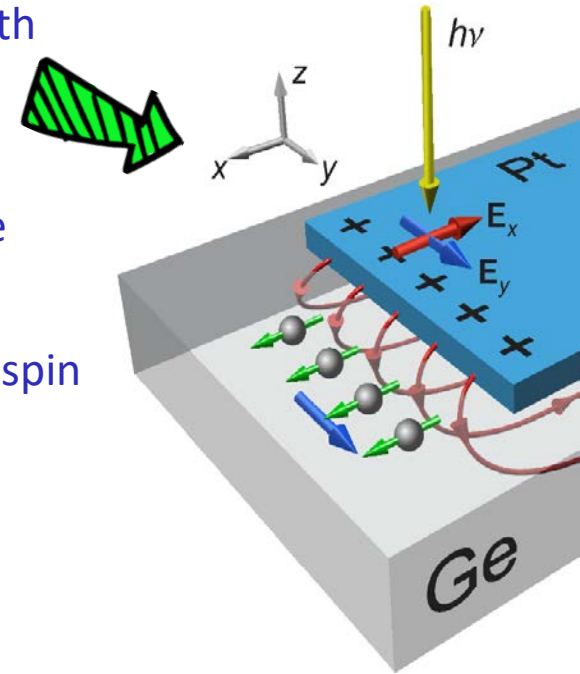


JRC with ST Microelectronics
Novel piezoelectric materials for MEMS

Spin transport in semiconductor-based platforms

The thesis work is focused on

- **Generation** of spin-polarized carriers in semiconductors with optical techniques
- **Detection** of spin-polarized carriers exploiting spin-charge interconversion phenomena (e.g., inverse spin-Hall, inverse Rashba-Edelstein)
- Investigation of spin-transport with the aim of **modulating** spin accumulation in non-local geometries



Selected literature:

Bottegoni et al., *Nature Mater.*, **13**, 790 (2014)

Bottegoni et al., *Phys. Rev. Lett.* **118**, 167402 (2017)

Zucchetti et al., *Phys. Rev. B* **98**, 184418 (2018)

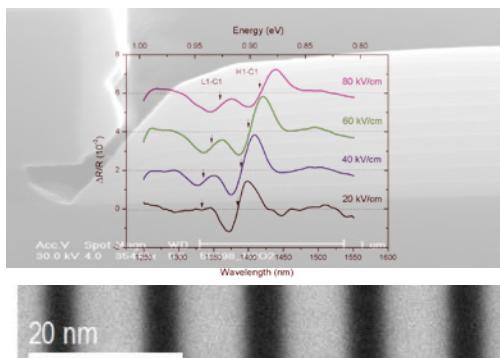
Marchionni et al., *Appl. Phys. Lett.* **118**, 212402 (2021)

Semiconductors nanostructures and devices: Strain engineering and quantum effects SiGe heterostructures



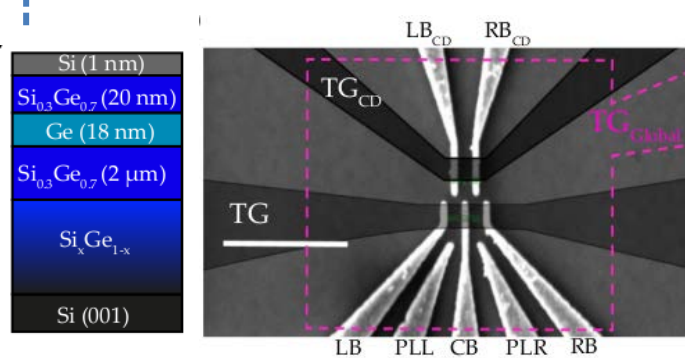
Como Campus

Mid-infrared non-linear effects in Ge QWs

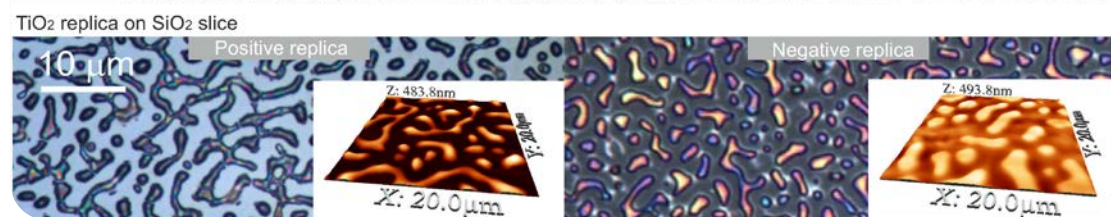
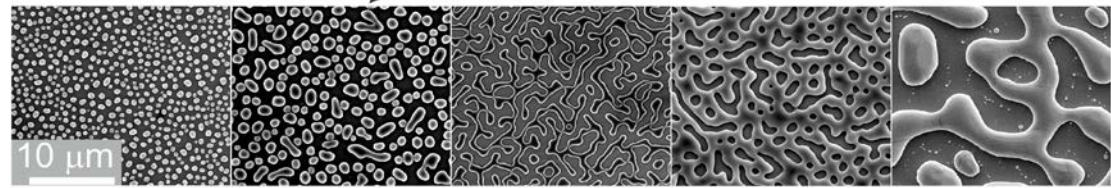
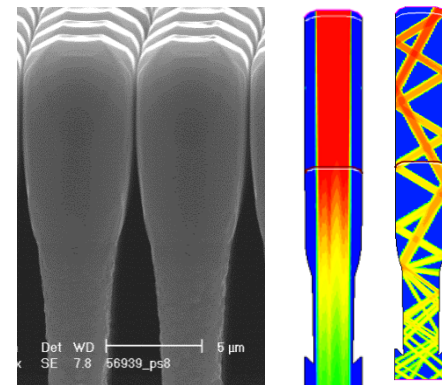


SiGe height, Ge content

2D Hole gas in Ge QWs for qubit implementation



Photodetectors based on Ge microcrystals

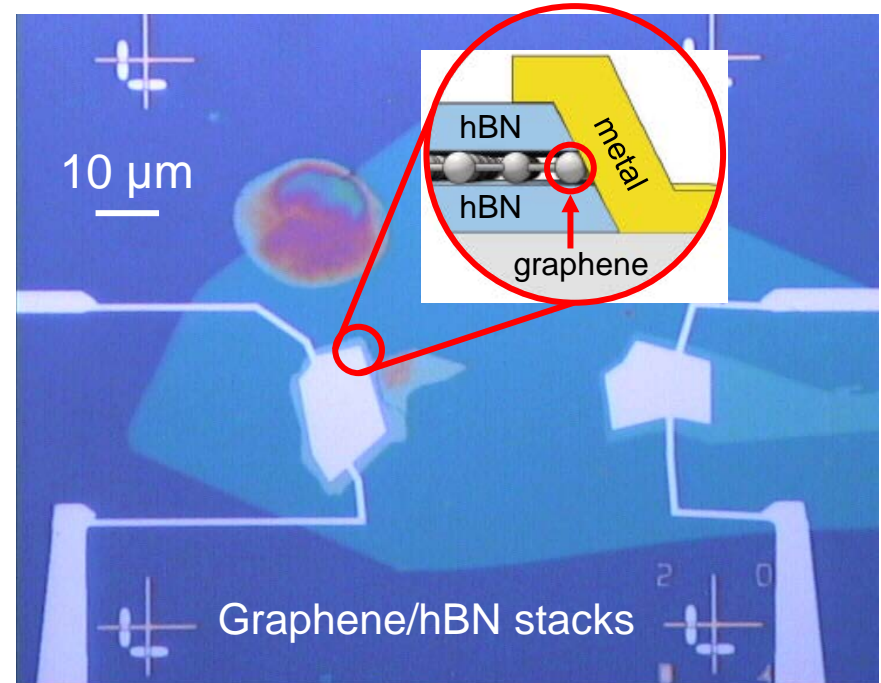


Dewetting instability in semiconductors materials and their applications by nanolithography

Visible Infrared dual band detectors



2D Nanoelectronics and Nanofabrication



The most advanced fully integrated 100 mm **e-beam lithography** system in Lombardy. It is placed in a clean room and features:

- Resolution down to 6 nm.
- Schottky field emission gun operated at 30 keV
- 100 mm laser interferometer stage (position error < 20 nm)
- Alignment error < 20 nm
- Automated laser height sensing (autofocus)

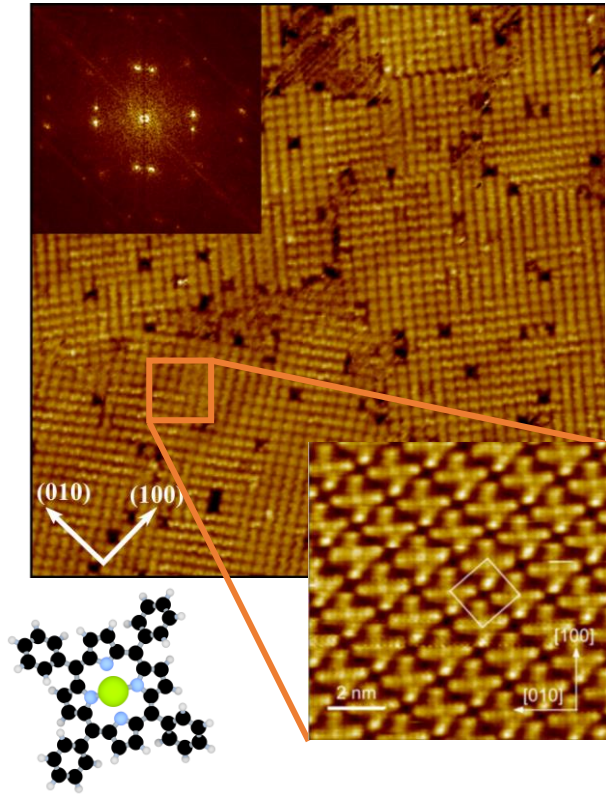
2D Materials in Nanoelectronics

2D nanoelectronic devices and circuits are realized by stacking 2D layers of:

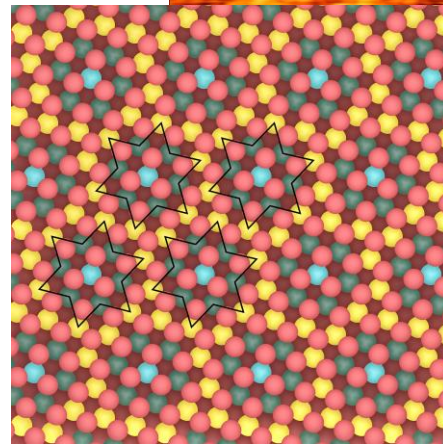
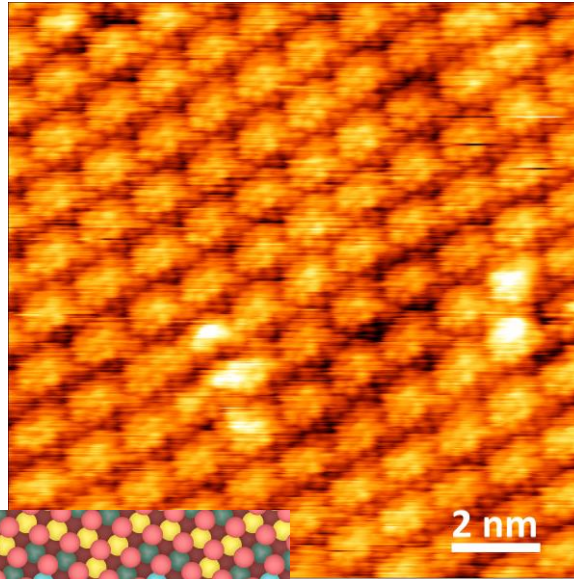
- Graphene (semimetal)
- MoS₂ and WSe₂ (semiconductors)
- hBN (insulator)

STM LAB

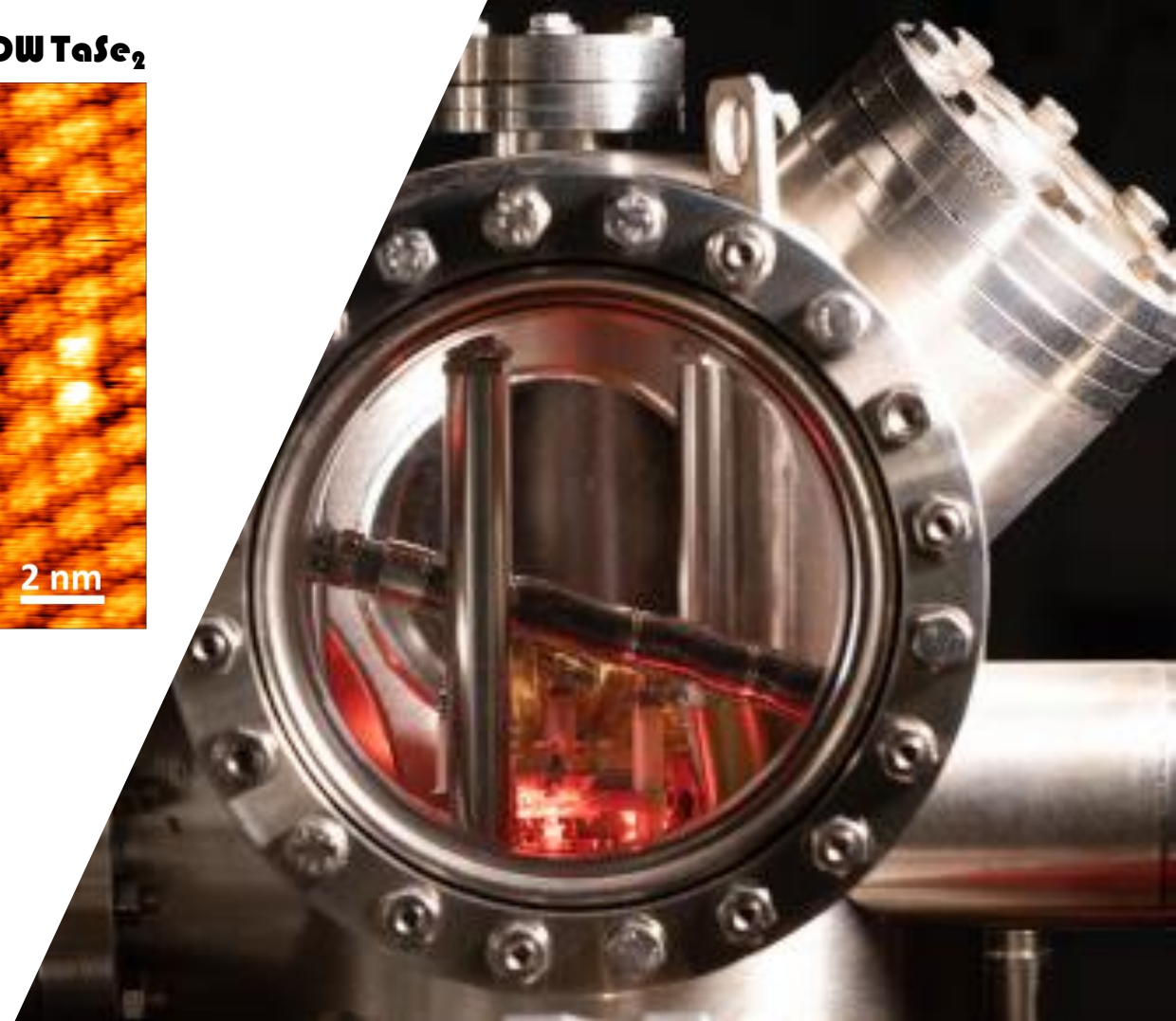
Co-TPP self assembly



Atomically resolved CDW TaSe_2



Sketch model

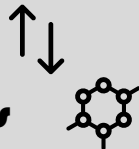


Research fields

Molecular Spintronics

low dimensional systems

Epitaxial Growth



we contribute to...

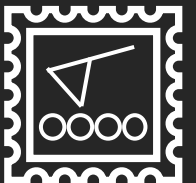


SINFONIA

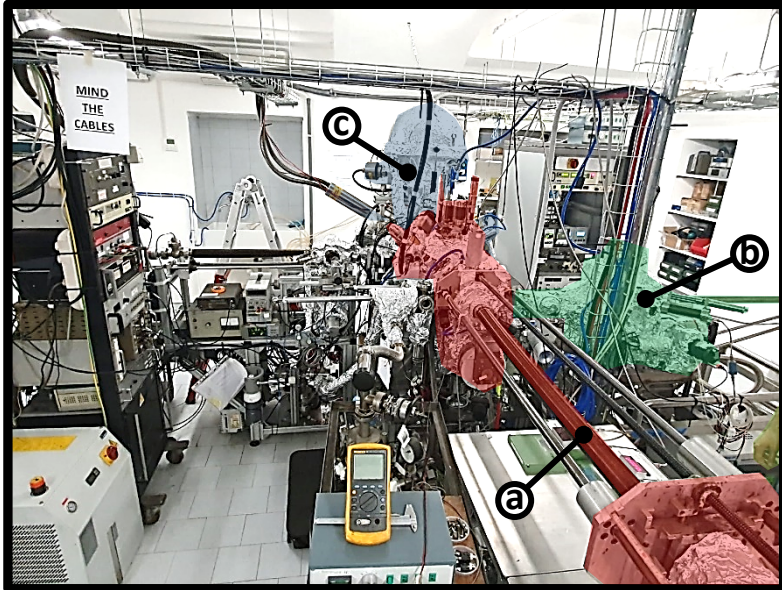
EU FET Open
H2020 project

Contact us

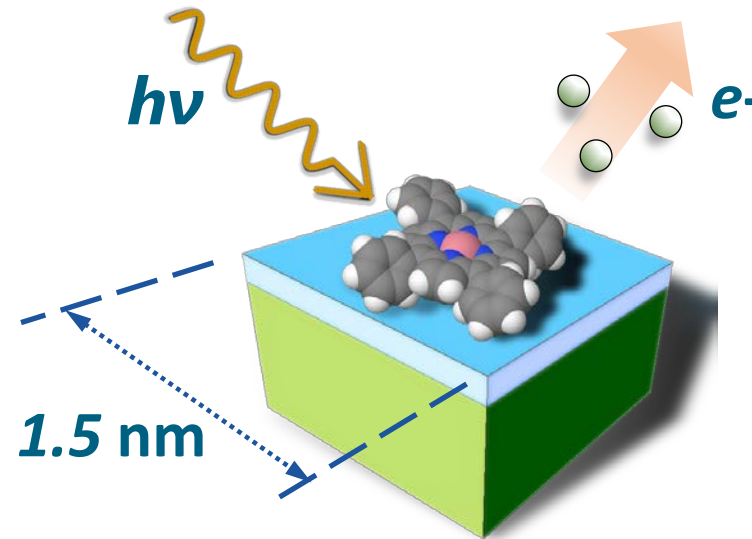
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Photoemission spectroscopies to explore nano-assembled molecular architectures



VESI laboratory: (a) sample preparation chamber, (b) OMBE chamber, (c) measurement chamber



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